

PE506BA

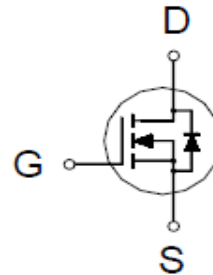
N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	6mΩ @ $V_{GS} = 10V$	38A



PDFN 3X3P



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ °C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current ³	$T_C = 25\text{ °C}$	I_D	38	A
	$T_C = 100\text{ °C}$		24	
	$T_A = 25\text{ °C}$		12	
	$T_A = 70\text{ °C}$		9.8	
Pulsed Drain Current ¹		I_{DM}	60	
Avalanche Current		I_{AS}	32	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	53	mJ
Power Dissipation	$T_C = 25\text{ °C}$	P_D	15.6	W
	$T_C = 100\text{ °C}$		6.3	
	$T_A = 25\text{ °C}$		1.6	
	$T_A = 70\text{ °C}$		1	
Operating Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$R_{\theta JA}$		77	°C / W
Junction-to-Case	$R_{\theta JC}$		8	

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25\text{ °C}$.

³Package limitation current is 19A.

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.6	3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V			1	μA
		V _{DS} = 20V, V _{GS} = 0V, T _J = 125 °C			10	
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 4.5V, I _D = 12A		6.2	9	mΩ
		V _{GS} = 10V, I _D = 12A		5.4	6	
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 12A		80		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz		1818		pF
Output Capacitance	C _{oss}			263		
Reverse Transfer Capacitance	C _{rss}			218		
Total Gate Charge ²	Q _{g(VGS=10V)}	V _{DS} = 15V, I _D = 12A		43.8		nC
	Q _{g(VGS=4.5V)}			23.1		
Gate-Source Charge ²	Q _{gs}			5.5		
Gate-Drain Charge ²	Q _{gd}			12.7		
Turn-On Delay Time ²	t _{d(on)}		V _{DD} = 15V, I _D ≅ 12A, V _{GS} = 10V, R _{GEN} = 6Ω		25	
Rise Time ²	t _r			24		
Turn-Off Delay Time ²	t _{d(off)}			99		
Fall Time ²	t _f			57		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current ³	I _S				13	A
Forward Voltage ¹	V _{SD}	I _F = 12A, V _{GS} = 0V			1.2	V
Reverse Recovery Time	t _{rr}	I _F = 12A, di _F /dt = 100A / μS V _{GS} = 0V		22		nS
Reverse Recovery Charge	Q _{rr}				12	

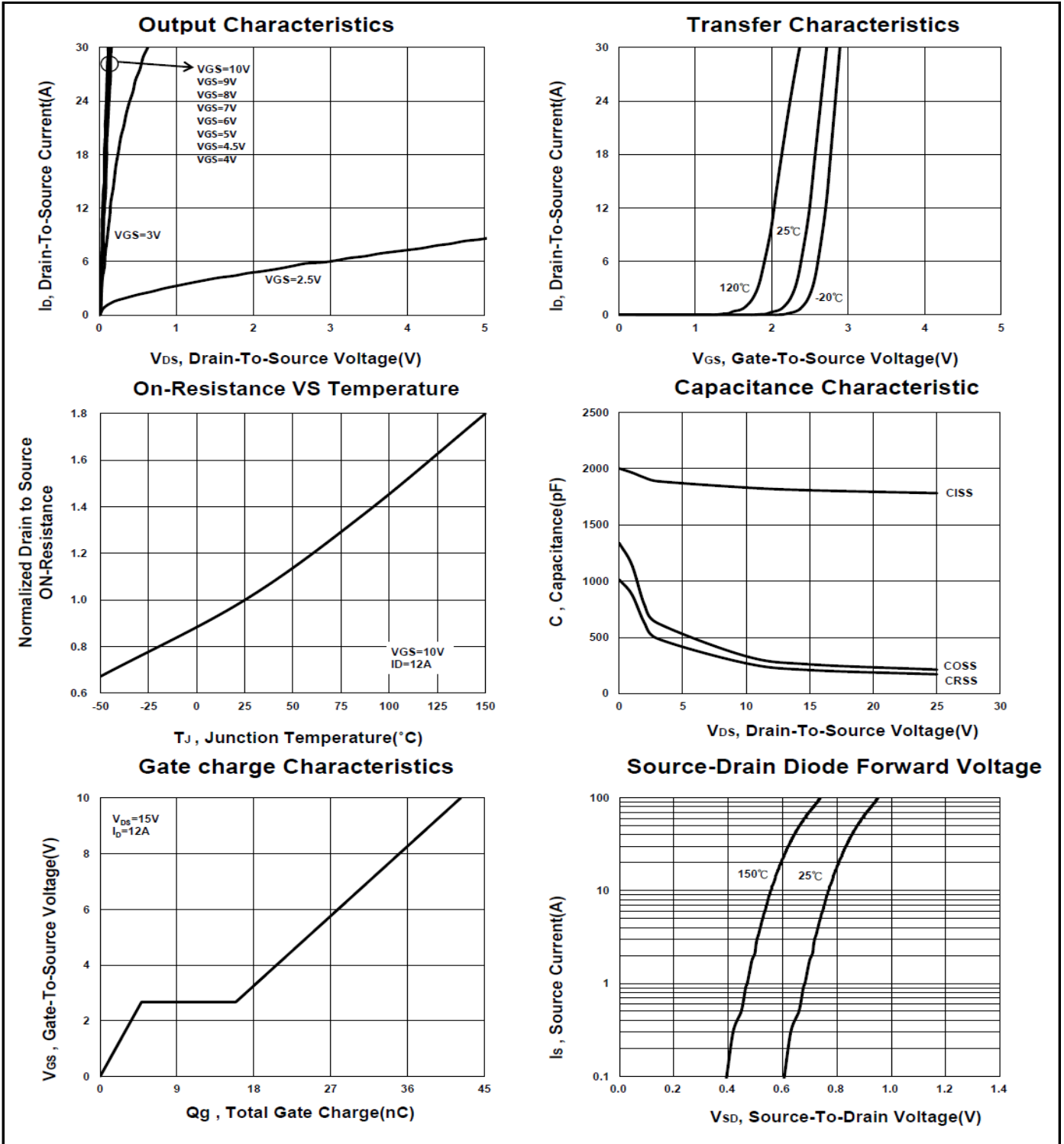
¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

³Package limitation current is 19A.

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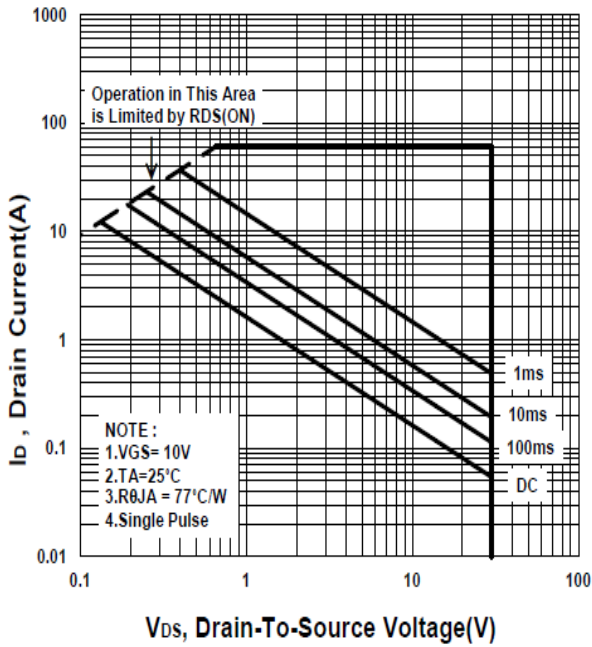
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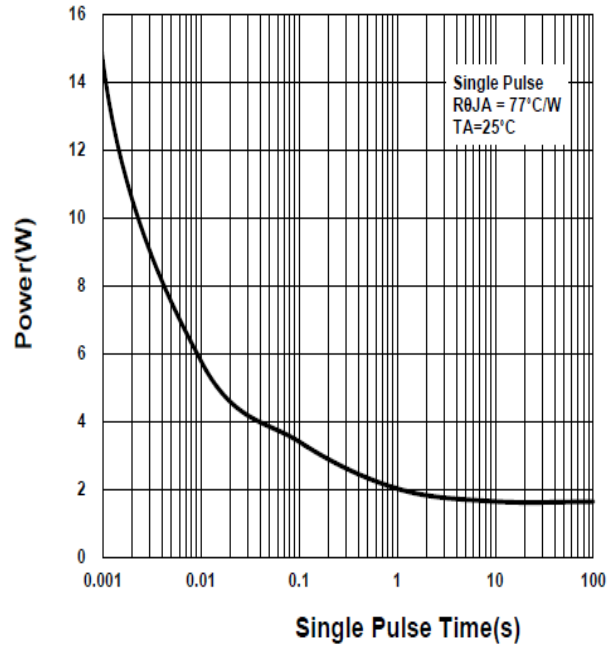
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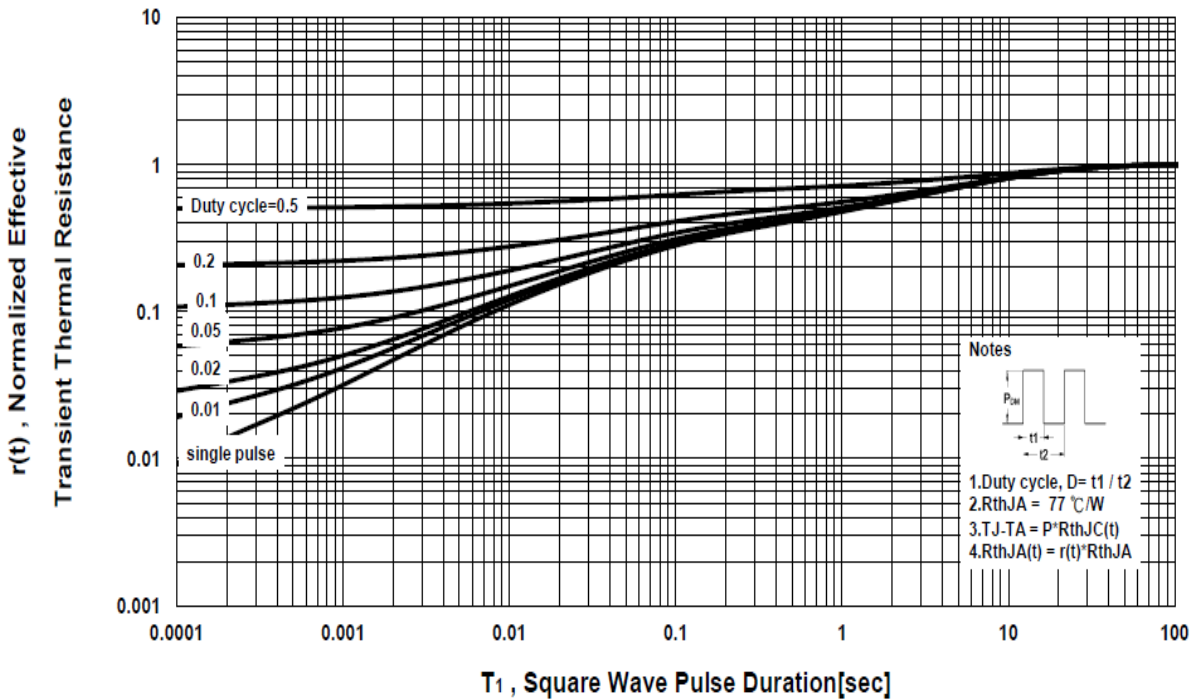
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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Package Dimension

PDFN 3x3P MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	3		3.6	I	0.7		1.12
B	2.88		3.2	J	0.1		0.33
C	2.9		3.2	K	0.6		
D	1.98		2.69	L	0°	10°	12°
E	3		3.6	M	0.14		0.41
F	0		0.455	N	0.6		0.7
G	1.47		2.2	O	0.12		0.36
H	0.15		0.56	P	0		0.2

